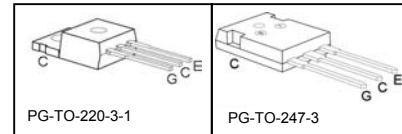
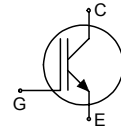


## High Speed IGBT in NPT-technology

- 30% lower  $E_{off}$  compared to previous generation
- Short circuit withstand time – 10  $\mu$ s
- Designed for operation above 30 kHz
- NPT-Technology for 600V applications offers:
  - parallel switching capability
  - moderate  $E_{off}$  increase with temperature
  - very tight parameter distribution
- High ruggedness, temperature stable behaviour
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC<sup>1</sup> for target applications
- Complete product spectrum and PSpice Models : <http://www.infineon.com/igbt/>



Type	$V_{CE}$	$I_C$	$E_{off}$	$T_j$	Marking	Package
SGP20N60HS	600V	20	240 $\mu$ J	150°C	G20N60HS	PG-TO-220-3-1
SGW20N60HS	600V	20	240 $\mu$ J	150°C	G20N60HS	PG-TO-247-3

### Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CE}$	600	V
DC collector current	$I_C$		A
$T_C = 25^\circ\text{C}$		36	
$T_C = 100^\circ\text{C}$		20	
Pulsed collector current, $t_p$ limited by $T_{jmax}$	$I_{Cpuls}$	80	
Turn off safe operating area $V_{CE} \leq 600\text{V}$ , $T_j \leq 150^\circ\text{C}$	-	80	
Avalanche energy single pulse $I_C = 20\text{A}$ , $V_{CC} = 50\text{V}$ , $R_{GE} = 25\Omega$ start $T_j = 25^\circ\text{C}$	$E_{AS}$	115	mJ
Gate-emitter voltage static transient ( $t_p < 1\mu\text{s}$ , $D < 0.05$ )	$V_{GE}$	$\pm 20$ $\pm 30$	V
Short circuit withstand time <sup>2)</sup> $V_{GE} = 15\text{V}$ , $V_{CC} \leq 600\text{V}$ , $T_j \leq 150^\circ\text{C}$	$t_{SC}$	10	$\mu\text{s}$
Power dissipation $T_C = 25^\circ\text{C}$	$P_{tot}$	178	W
Operating junction and storage temperature	$T_j$ , $T_{stg}$	-55...+150	$^\circ\text{C}$
Time limited operating junction temperature for $t < 150\text{h}$	$T_{j(tl)}$	175	
Soldering temperature, 1.6mm (0.063 in.) from case for 10s	-	260	

<sup>1</sup> J-STD-020 and JESD-022

<sup>2)</sup> Allowed number of short circuits: <1000; time between short circuits: >1s.

### Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
<b>Characteristic</b>				
IGBT thermal resistance, junction – case	$R_{thJC}$		0.7	K/W
Thermal resistance, junction – ambient	$R_{thJA}$	PG-TO-220-3-1 PG-TO-247-3-21	62 40	

### Electrical Characteristic, at $T_j = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
<b>Static Characteristic</b>						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=500\mu A$	600	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE} = 15V, I_C=20A$ $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$		2.8 3.5	3.15 4.00	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=500\mu A, V_{CE}=V_{GE}$	3	4	5	
Zero gate voltage collector current	$I_{CES}$	$V_{CE}=600V, V_{GE}=0V$ $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$	- -	- -	40 2500	$\mu A$
Gate-emitter leakage current	$I_{GES}$	$V_{CE}=0V, V_{GE}=20V$	-	-	100	nA
Transconductance	$g_{fs}$	$V_{CE}=20V, I_C=20A$	-	14		S

### Dynamic Characteristic

Input capacitance	$C_{iss}$	$V_{CE}=25V,$	-	1100		pF
Output capacitance	$C_{oss}$	$V_{GE}=0V,$	-	105		
Reverse transfer capacitance	$C_{rfs}$	$f=1\text{MHz}$	-	64		
Gate charge	$Q_{Gate}$	$V_{CC}=480V, I_C=20A$ $V_{GE}=15V$	-	100		nC
Internal emitter inductance measured 5mm (0.197 in.) from case	$L_E$	PG-TO-220-3-1 PG-TO-247-3-21	-	7 13		nH
Short circuit collector current <sup>1)</sup>	$I_{C(SC)}$	$V_{GE}=15V, t_{SC}\leq 10\mu s$ $V_{CC}\leq 600V,$ $T_j\leq 150^\circ\text{C}$	-	170		A

<sup>1)</sup> Allowed number of short circuits: <1000; time between short circuits: >1s.

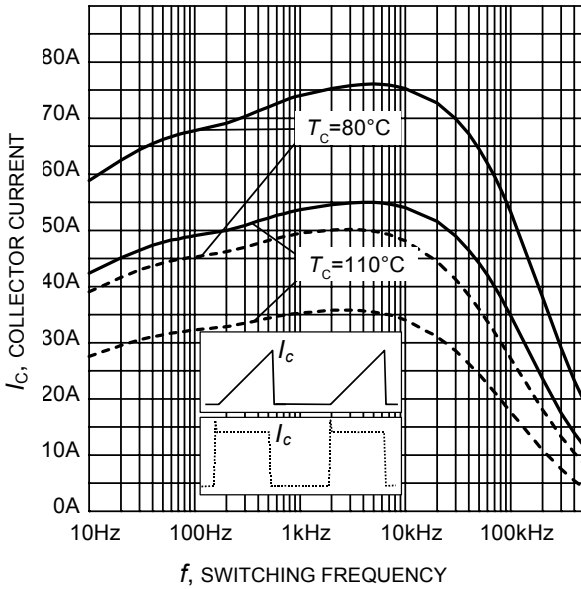
### Switching Characteristic, Inductive Load, at $T_j=25^\circ\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>IGBT Characteristic</b>						
Turn-on delay time	$t_{d(on)}$	$T_j=25^\circ\text{C}$ , $V_{CC}=400\text{V}$ , $I_C=20\text{A}$ , $V_{GE}=0/15\text{V}$ , $R_G=16\Omega$ $L_{\sigma}^{1)}$ = 60nH, $C_{\sigma}^{1)}$ = 40pF Energy losses include "tail" and diode reverse recovery.	-	18		ns
Rise time	$t_r$		-	15		
Turn-off delay time	$t_{d(off)}$		-	207		
Fall time	$t_f$		-	13		
Turn-on energy	$E_{on}$		-	0.39		mJ
Turn-off energy	$E_{off}$		-	0.30		
Total switching energy	$E_{ts}$		-	0.69		

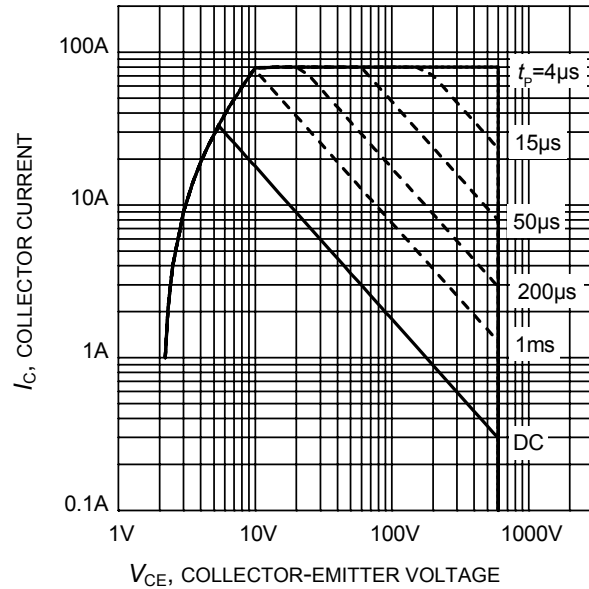
### Switching Characteristic, Inductive Load, at $T_j=150^\circ\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>IGBT Characteristic</b>						
Turn-on delay time	$t_{d(on)}$	$T_j=150^\circ\text{C}$ $V_{CC}=400\text{V}$ , $I_C=20\text{A}$ , $V_{GE}=0/15\text{V}$ , $R_G=2.2\Omega$ $L_{\sigma}^{1)}$ = 60nH, $C_{\sigma}^{1)}$ = 40pF Energy losses include "tail" and diode reverse recovery.	-	15		ns
Rise time	$t_r$		-	8.5		
Turn-off delay time	$t_{d(off)}$		-	65		
Fall time	$t_f$		-	35		
Turn-on energy	$E_{on}$		-	0.46		mJ
Turn-off energy	$E_{off}$		-	0.24		
Total switching energy	$E_{ts}$		-	0.7		
Turn-on delay time	$t_{d(on)}$	$T_j=150^\circ\text{C}$ $V_{CC}=400\text{V}$ , $I_C=20\text{A}$ , $V_{GE}=0/15\text{V}$ , $R_G=16\Omega$ $L_{\sigma}^{1)}$ = 60nH, $C_{\sigma}^{1)}$ = 40pF Energy losses include "tail" and diode reverse recovery.	-	17		ns
Rise time	$t_r$		-	13		
Turn-off delay time	$t_{d(off)}$		-	222		
Fall time	$t_f$		-	13		
Turn-on energy	$E_{on}$		-	0.6		mJ
Turn-off energy	$E_{off}$		-	0.36		
Total switching energy	$E_{ts}$		-	0.96		

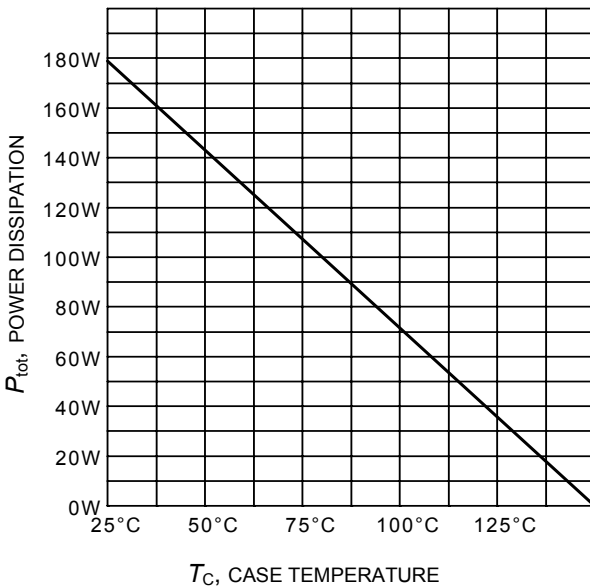
<sup>1)</sup> Leakage inductance  $L_{\sigma}$  and Stray capacity  $C_{\sigma}$  due to test circuit in Figure E.



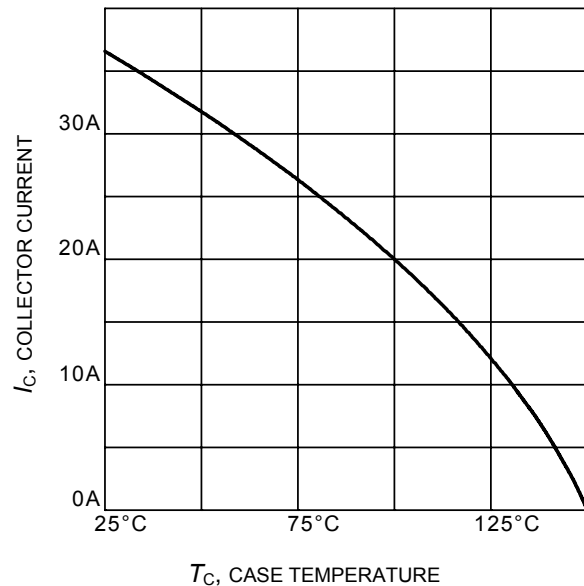
**Figure 1. Collector current as a function of switching frequency**  
 $(T_j \leq 150^\circ\text{C}, D = 0.5, V_{CE} = 400\text{V}, V_{GE} = 0/+15\text{V}, R_G = 16\Omega)$



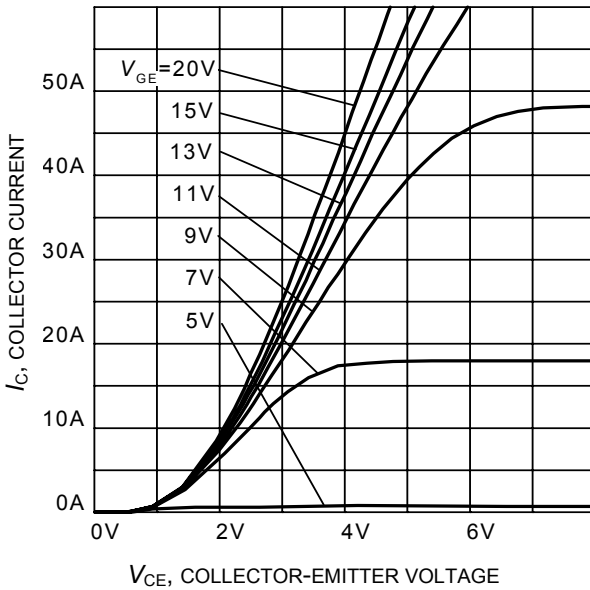
**Figure 2. Safe operating area**  
 $(D = 0, T_C = 25^\circ\text{C}, T_j \leq 150^\circ\text{C}; V_{GE} = 15\text{V})$



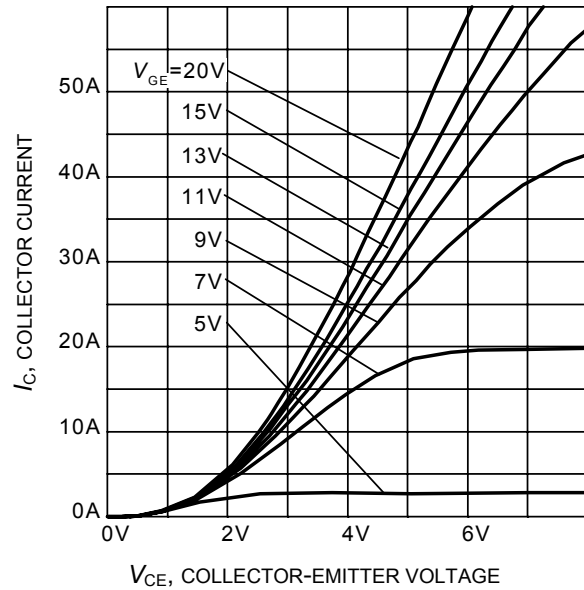
**Figure 3. Power dissipation as a function of case temperature**  
 $(T_j \leq 150^\circ\text{C})$



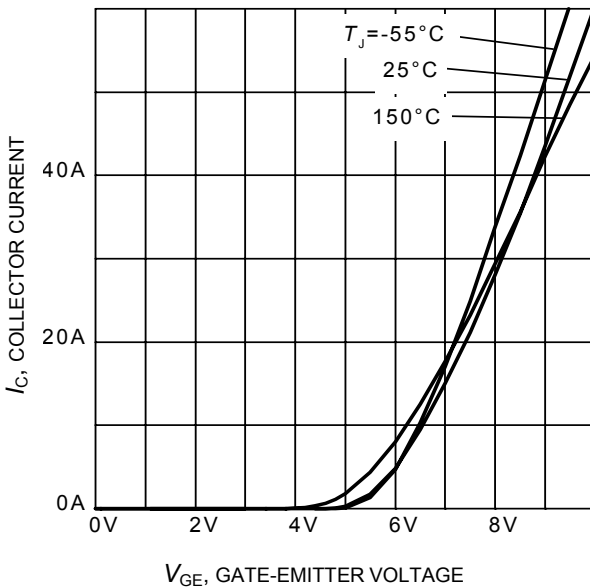
**Figure 4. Collector current as a function of case temperature**  
 $(V_{GE} \leq 15\text{V}, T_j \leq 150^\circ\text{C})$



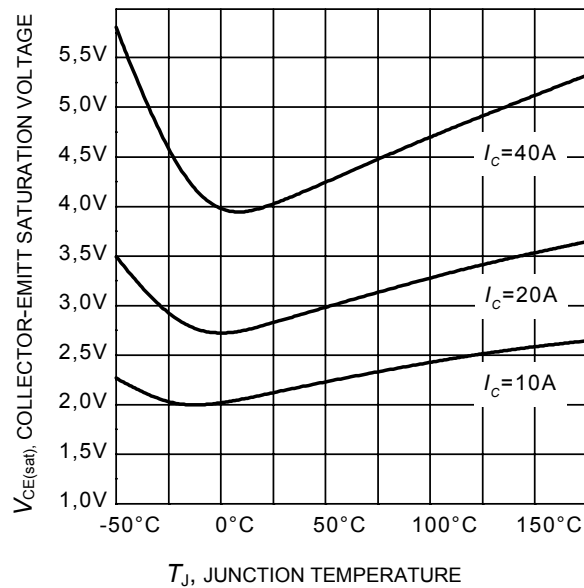
**Figure 5. Typical output characteristic**  
( $T_j = 25^\circ\text{C}$ )



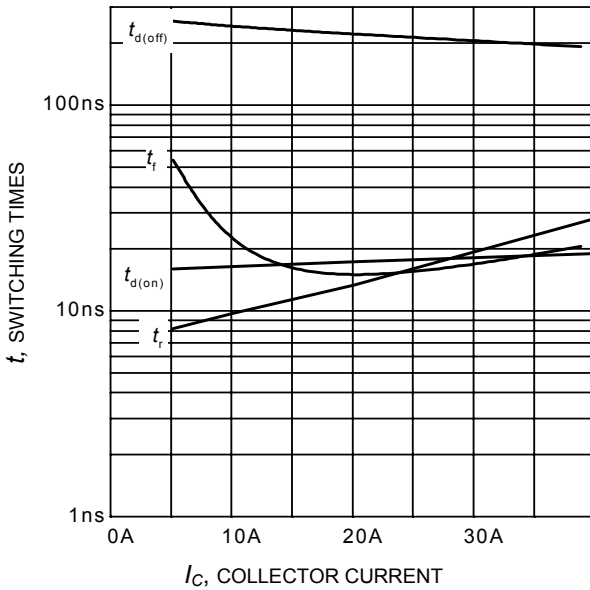
**Figure 6. Typical output characteristic**  
( $T_j = 150^\circ\text{C}$ )



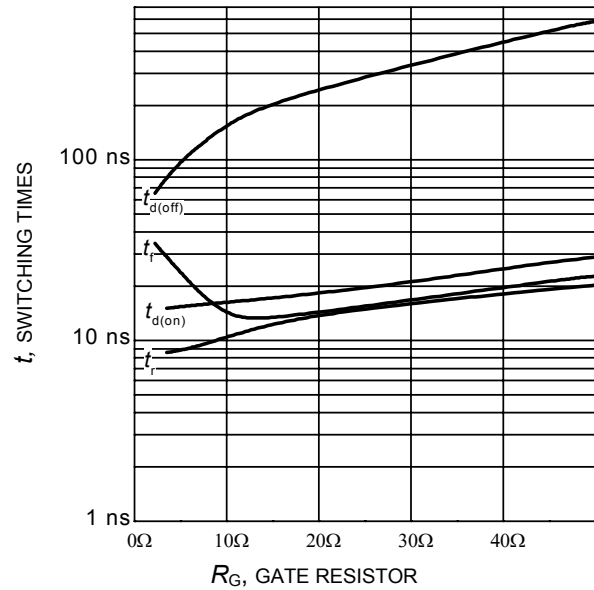
**Figure 7. Typical transfer characteristic**  
( $V_{CE} = 10\text{V}$ )



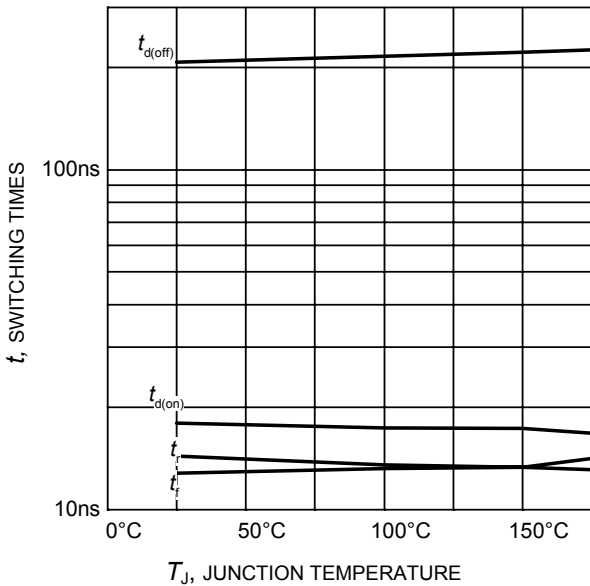
**Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature**  
( $V_{GE} = 15\text{V}$ )



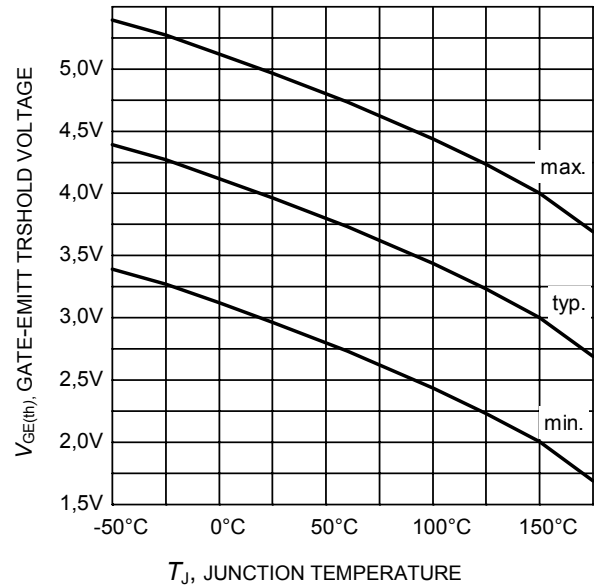
**Figure 9. Typical switching times as a function of collector current**  
(inductive load,  $T_J=150^{\circ}\text{C}$ ,  $V_{CE}=400\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $R_G=16\Omega$ , Dynamic test circuit in Figure E)



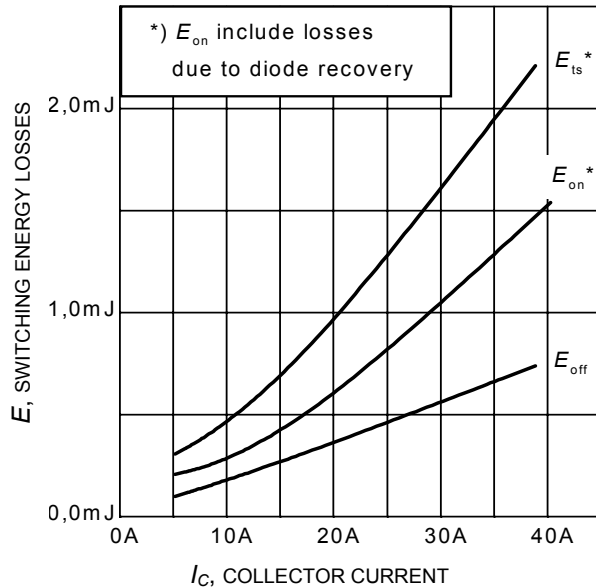
**Figure 10. Typical switching times as a function of gate resistor**  
(inductive load,  $T_J=150^{\circ}\text{C}$ ,  $V_{CE}=400\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $I_C=20\text{A}$ , Dynamic test circuit in Figure E)



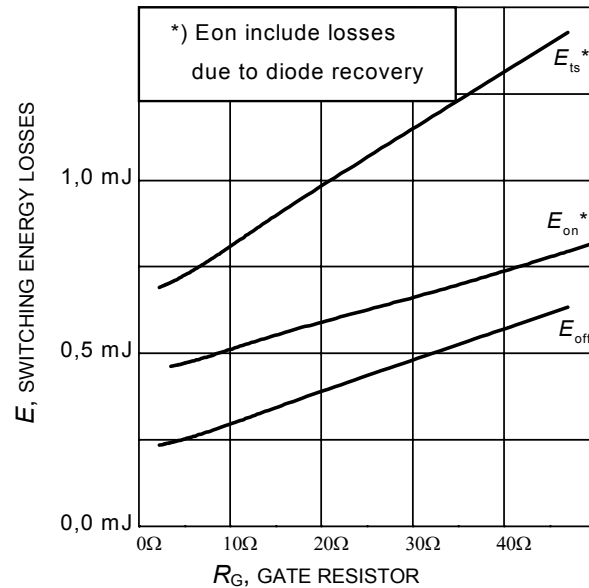
**Figure 11. Typical switching times as a function of junction temperature**  
(inductive load,  $V_{CE}=400\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $I_C=20\text{A}$ ,  $R_G=16\Omega$ , Dynamic test circuit in Figure E)



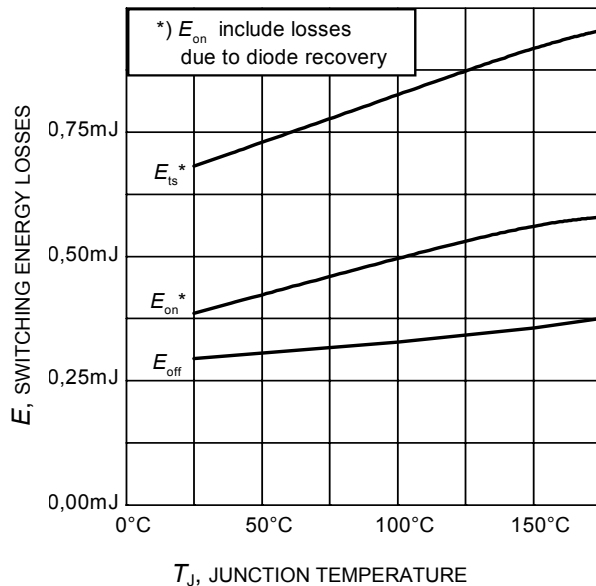
**Figure 12. Gate-emitter threshold voltage as a function of junction temperature**  
( $I_C = 0.5\text{mA}$ )



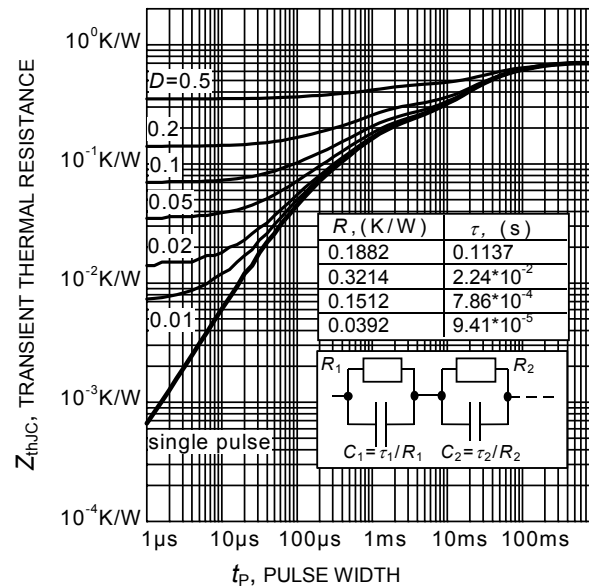
**Figure 13. Typical switching energy losses as a function of collector current**  
(inductive load,  $T_J=150^\circ\text{C}$ ,  $V_{CE}=400\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $R_G=16\Omega$ , Dynamic test circuit in Figure E)



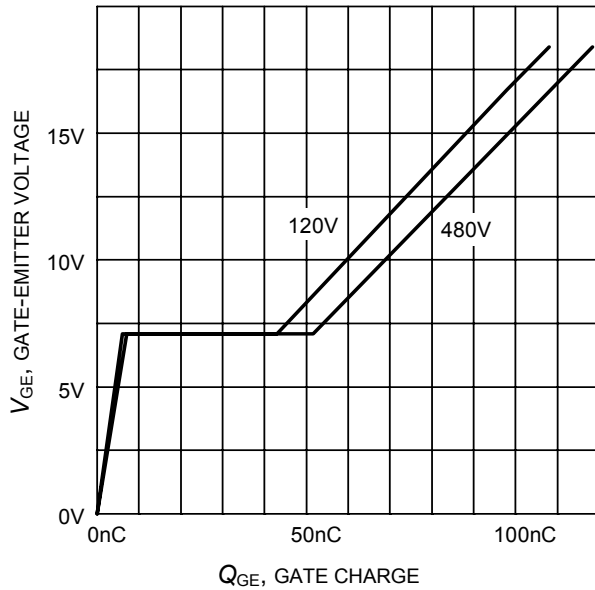
**Figure 14. Typical switching energy losses as a function of gate resistor**  
(inductive load,  $T_J=150^\circ\text{C}$ ,  $V_{CE}=400\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $I_C=20\text{A}$ , Dynamic test circuit in Figure E)



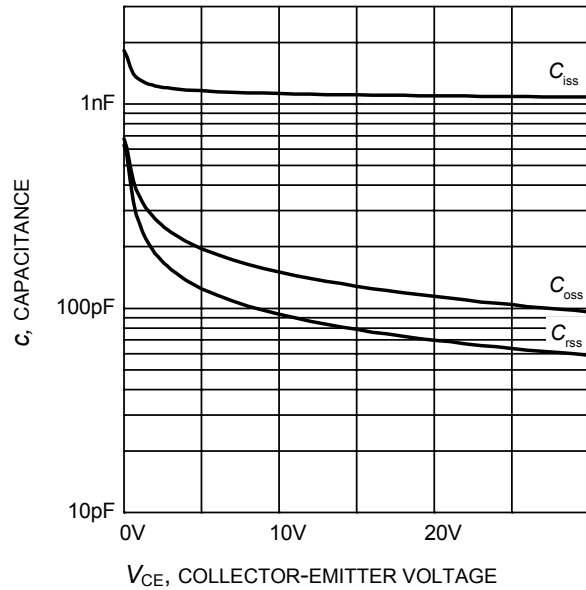
**Figure 15. Typical switching energy losses as a function of junction temperature**  
(inductive load,  $V_{CE}=400\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $I_C=20\text{A}$ ,  $R_G=16\Omega$ , Dynamic test circuit in Figure E)



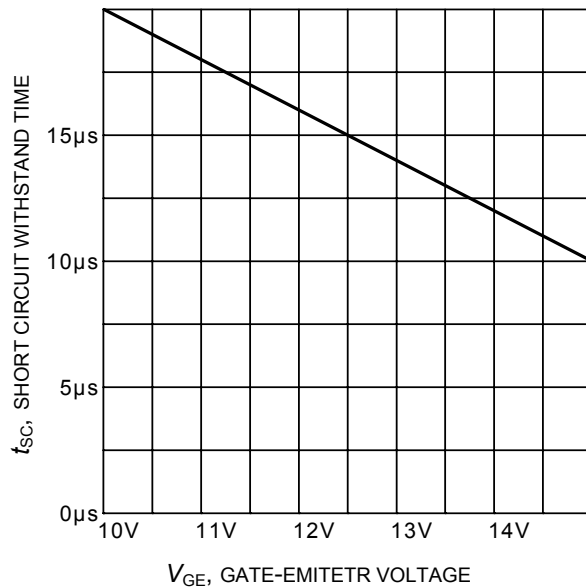
**Figure 16. IGBT transient thermal resistance**  
( $D = t_p / T$ )



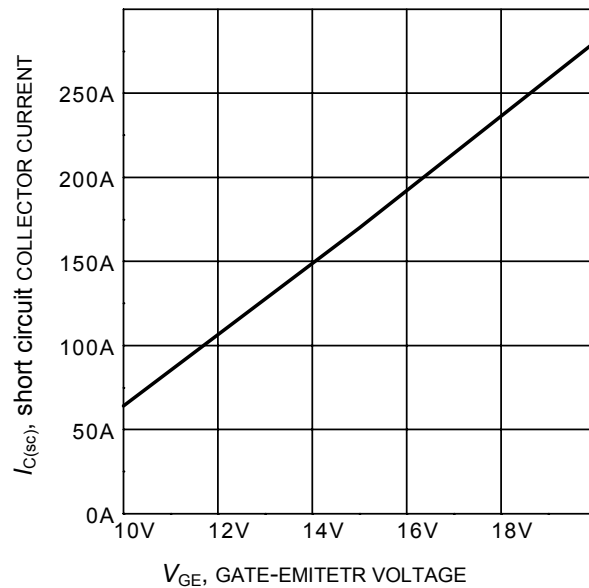
**Figure 17. Typical gate charge**  
( $I_C=20\text{ A}$ )



**Figure 18. Typical capacitance as a function of collector-emitter voltage**  
( $V_{GE}=0\text{V}$ ,  $f=1\text{ MHz}$ )



**Figure 19. Short circuit withstand time as a function of gate-emitter voltage**  
( $V_{CE}=600\text{V}$ , start at  $T_J=25^\circ\text{C}$ )

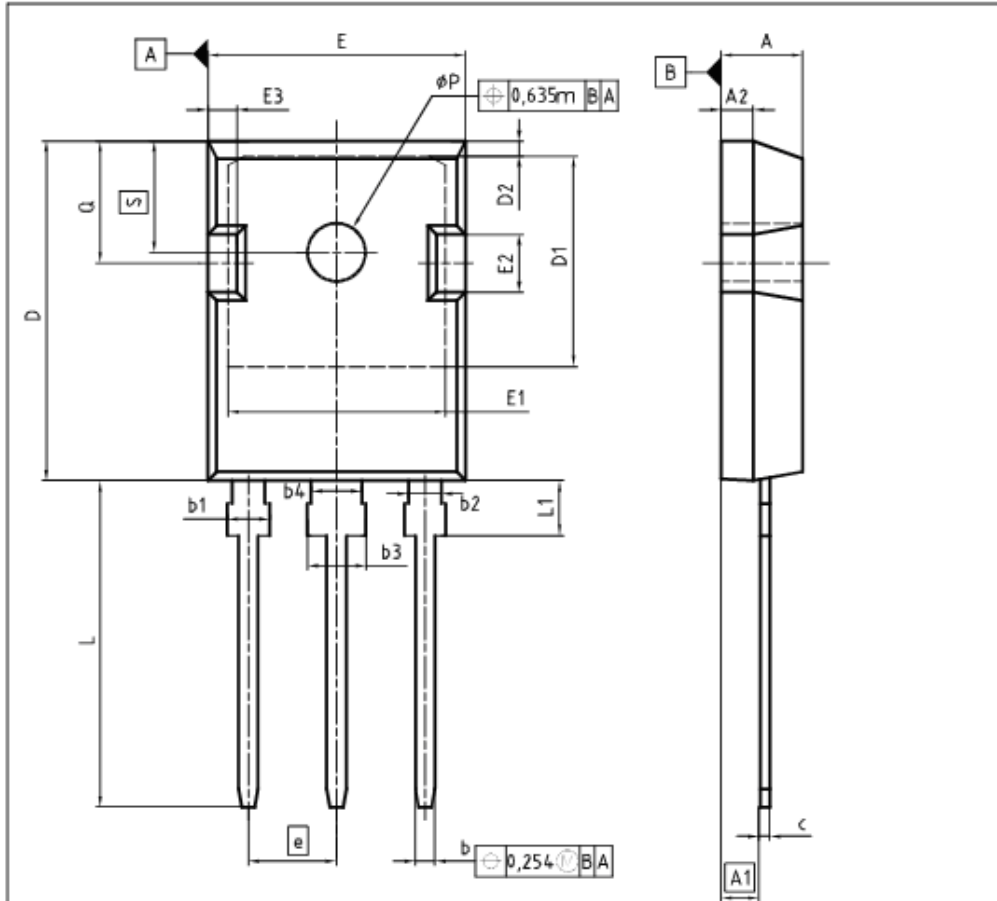


**Figure 20. Typical short circuit collector current as a function of gate-emitter voltage**  
( $V_{CE} \leq 600\text{V}$ ,  $T_J \leq 150^\circ\text{C}$ )





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DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.83	5.21	0.180	0.205
A1	2.27	2.54	0.089	0.100
A2	1.85	2.16	0.073	0.085
b	1.07	1.33	0.042	0.052
b1	1.90	2.41	0.075	0.095
b2	1.90	2.16	0.075	0.085
b3	2.87	3.38	0.113	0.133
b4	2.87	3.13	0.113	0.123
c	0.55	0.68	0.022	0.027
D	20.80	21.10	0.819	0.831
D1	16.25	17.65	0.640	0.695
D2	0.95	1.35	0.037	0.053
E	15.70	16.13	0.618	0.635
E1	13.10	14.15	0.516	0.557
E2	3.68	5.10	0.145	0.201
E3	1.00	2.60	0.039	0.102
e	5.44		0.214	
N	3		3	
L	19.80	20.32	0.780	0.800
L1	4.10	4.47	0.161	0.176
phi P	3.50	3.70	0.138	0.146
Q	5.49	6.00	0.216	0.236
S	6.04	6.30	0.238	0.248

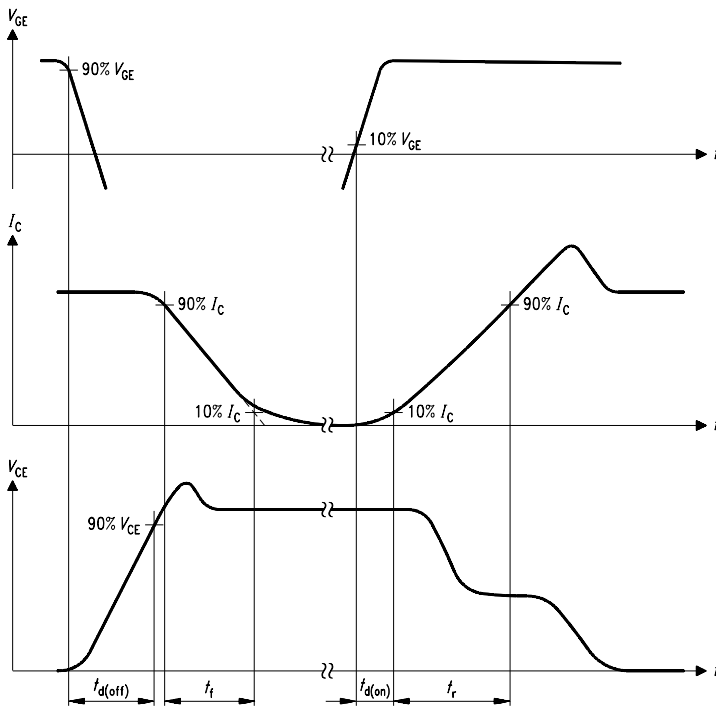
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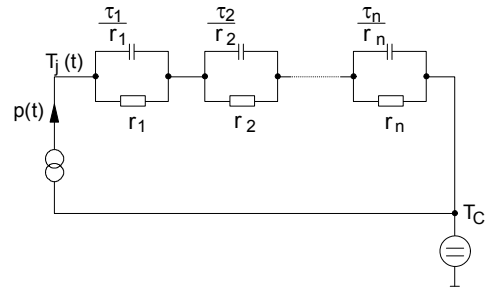
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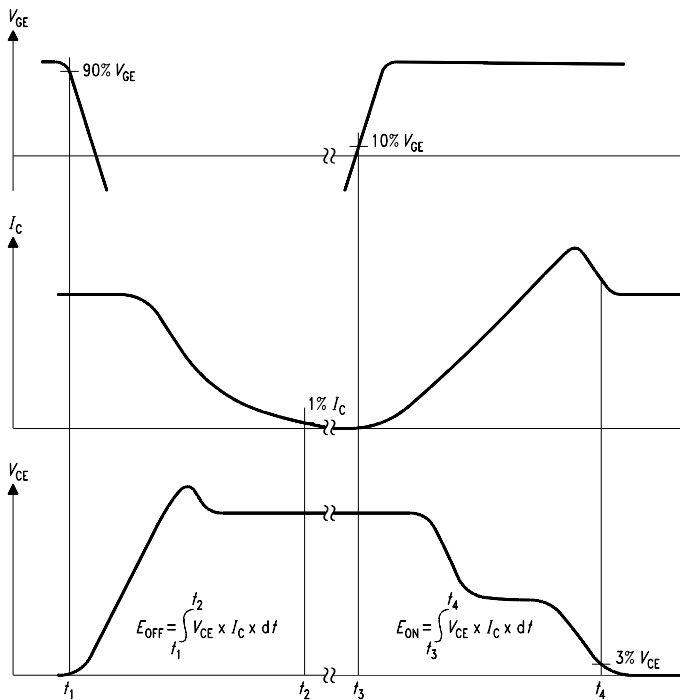


**Figure A. Definition of switching times**

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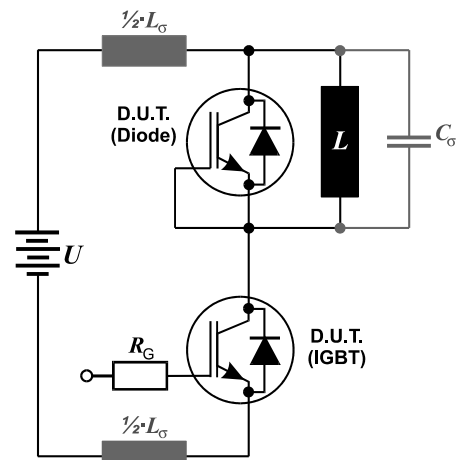


**Figure D. Thermal equivalent circuit**



**Figure B. Definition of switching losses**

SIS



**Figure E. Dynamic test circuit**  
Leakage inductance  $L_\sigma = 60\text{nH}$   
and Stray capacity  $C_\sigma = 40\text{pF}$ .

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